

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13	(drain near electrode) near10 portion near10 uneven	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:37
L2	618	(drain near electrode) near10 ((first or second or two) adj portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:37
L3	430	(pixel adj electrode) and (drain near electrode) near10 ((first or second or two) adj portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:38
L4	395	(pixel adj electrode) and (drain near electrode) near10 ((first or second or two) adj portion) and ((semiconductor or silicon or active) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:38
L5	395	(pixel adj electrode) and ((drain near electrode) near10 ((first or second or two) adj portion)) and ((semiconductor or silicon or active) near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:39
L6	376	(pixel adj electrode) and ((drain near electrode) near10 ((first or second or two) adj portion)) and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:39
L7	288	(pixel adj electrode) and ((drain near electrode) near10 ((first or second or two) adj portion)) and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode) and (ohmic adj contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:39
L8	283	(pixel adj electrode) and ((drain near electrode) near10 ((first or second or two) adj portion)) and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode) and (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:40

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L9	128	(pixel adj electrode) and ((drain near electrode) near10 ((first or second or two) adj portion)).clm. and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode) and (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:42
L10	110	(pixel adj electrode) and ((drain near electrode) near5((first or second or two) adj portion)).clm. and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode) and (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:43
L11	74	(pixel adj electrode) and ((drain near electrode) near2 ((first or second or two) adj portion)).clm. and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode) and (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:45
L12	35	(pixel adj electrode) same ((drain near electrode) near2 ((first or second or two) adj portion)).clm. and ((semiconductor or silicon or active) near (layer or film)) and (source adj electrode) and (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:45
L13	30	(pixel adj electrode) same ((drain near electrode) near2 ((first or second or two) adj portion)) same ((semiconductor or silicon or active) near (layer or film)) same (source adj electrode) and (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:45
L14	23	(pixel adj electrode) same ((drain near electrode) near2 ((first or second or two) adj portion)) same ((semiconductor or silicon or active) near (layer or film)) same (source adj electrode) same (ohmic adj contact) and ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:46

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L15	22	(pixel adj electrode) same ((drain near electrode) near2 ((first or second or two) adj portion)) same ((semiconductor or silicon or active) near (layer or film)) same (source adj electrode) same (ohmic adj contact) same ((data or gate or signal) near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:49
L16	36	18 and ((drain adj electrode) near10 (width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:50
L17	15	18 and ((drain adj electrode) near10 portion near10 (width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:59
L18	369	method.clm. and (ohmic near contact).clm. and ((data or gate or signal) adj line).clm. and (source adj electrode).clm. and (drain adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:00
L19	318	method.clm. and (ohmic near contact).clm. and ((data or gate or signal) adj line).clm. and (source adj electrode).clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and ((semiconductor or active or silicon) adj (layer or film)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:02
L20	170	method.clm. and (ohmic near contact).clm. and ((data or gate or signal) adj line).clm. and (source adj electrode).clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and ((semiconductor or active or silicon) adj (layer or film)).clm. and ((drain adj electrode) near5 portion).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:02

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L21	65	method.clm. and (ohmic near contact).clm. and ((data or gate or signal) adj line).clm. and (source adj electrode).clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and ((semiconductor or active or silicon) adj (layer or film)).clm. and ((drain adj electrode) near5 ((first or second or two) near portion)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:03
L22	50	method.clm. and (ohmic near contact).clm. and ((data or gate or signal) adj line).clm. and (source adj electrode).clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and ((semiconductor or active or silicon) adj (layer or film)).clm. and ((drain adj electrode) near2 ((first or second or two) near portion)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:16
L23	5674	(drain adj electrode) near5 portion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:17
L24	114	(drain adj electrode) near5 portion near5 width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:17
L25	35	((drain adj electrode) near5 portion near5 width).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:17
L26	35	((drain adj electrode) near5 portion near5 width).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:19
L27	6	((drain adj electrode) near5 ((first or second or two) near portion) near5 width).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:24

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L28	91	((drain adj electrode) near5 shaped).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:28
L29	348	((drain adj electrode) near2 shaped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:28
L30	116	((drain adj electrode) near2 shaped) and (pixel adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:28
L31	116	((drain adj electrode) near2 shaped) and (pixel adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:28
L32	13	("20010030719" "4827146" "4902638" "5414283" "5414427" "5656824" "5808317" "5874746" "5929489" "6057904" "6256077" "6310668" "6320221").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 16:35
L33	5	("6664569").URPN.	USPAT	OR	ON	2007/01/05 16:36
L50	431	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:43
L51	355	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm. and method.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:43

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L52	280	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm. and method.clm. and ((drain adj electrode) near5 (portion or shape or shaped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:45
L53	227	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm. and method.clm. and ((drain adj electrode) near2 (portion or shape or shaped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:46
L54	123	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm. and method.clm. and ((drain adj electrode) near2 (portion or shape or shaped)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:47
L55	43	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm. and method.clm. and ((drain adj electrode) near2 (portion or shape or shaped) with (pixel adj electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:48

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L56	32	(gate adj electrode).clm. and ((gate or source or signal or data) near line).clm. and ((semiconductor or active or silicon) near (film or layer)).clm. and (ohmic adj contact).clm. and (drain adj electrode).clm. and (source adj electrode).clm. and method.clm. and ((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:51
L57	150	((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:54
L58	264	((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)) and ((drain adj electrode) near5 (thin or thinner or width or wider))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:54
L59	268	((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)) and ((drain adj electrode) near5 (thin or thinner or width or wider or larger))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:55
L60	38	((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)) and ((drain adj electrode) near5 (thin or thinner or width or wider or larger) near5 (portio or region or section))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:55
L61	117	((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)) and ((drain adj electrode) near5 (thin or thinner or width or wider or larger) near5 (portion or region or section))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 16:58
L62	8	((drain adj electrode) near2 (portion or shape or shaped) near10 (pixel adj electrode)) and ((drain adj electrode) near5 (thin or thinner or width or wider or larger) near5 (portion or region or section)) and ((drain adj electrode) near10 (third near portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:10

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L63	134	(drain adj electrode) near10 (third near portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:11
L64	82	(drain adj electrode) near5 (third near portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:12
L65	48	((drain adj electrode) near5 (third near portion)) and (pixel adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:15
L66	1912	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:16
L67	461	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:16
L68	441	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:16
L69	375	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:17
L70	343	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:20

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L71	230	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm. and (gate adj electrode).clm. and ((drain adj electrode) near2 (shape or shaped or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:21
L72	55	method.clm. and (drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm. and (gate adj electrode).clm. and ((drain adj electrode) near2 (shape or shaped or portion) near10 (wide or wider or larger or thin or thinner or width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:25
L73	55	method.clm. and (drain adj electrode).clm. and (pixel adj electrode) and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm. and (gate adj electrode).clm. and ((drain adj electrode) near2 (shape or shaped or portion) near10 (wide or wider or larger or thin or thinner or width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:24
L74	74	(drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact).clm. and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm. and (gate adj electrode).clm. and ((drain adj electrode) near2 (shape or shaped or portion) near10 (wide or wider or larger or thin or thinner or width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:26

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L75	118	(drain adj electrode).clm. and (pixel adj electrode).clm. and (ohmic adj contact) and ((semiconductor or active or silicon) adj (film or layer)).clm. and ((gate or source or data or signal) adj line).clm. and (gate adj electrode).clm. and ((drain adj electrode) near2 (shape or shaped or portion) near10 (wide or wider or larger or thin or thinner or width))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 17:26
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